

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

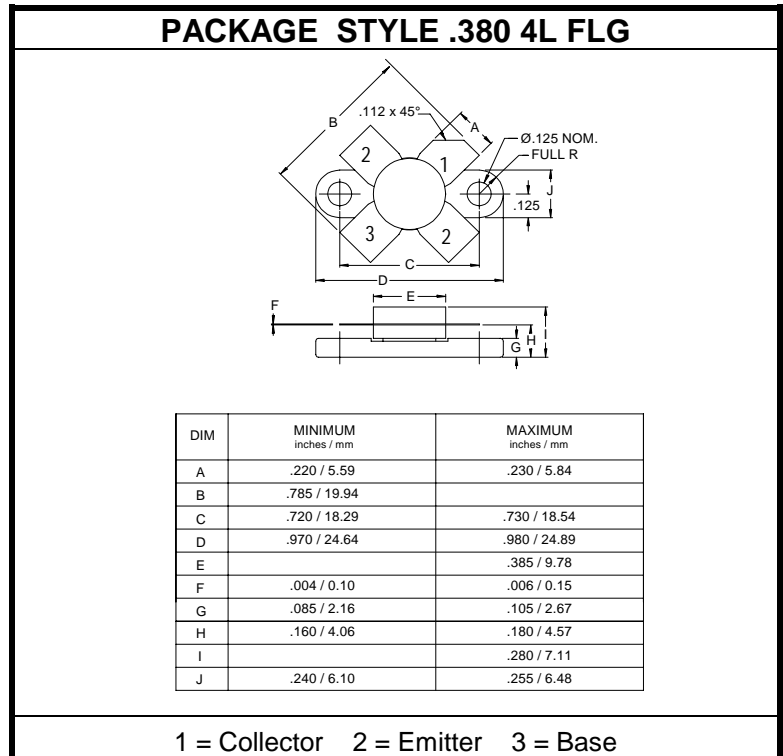
The **ASI CD2315** is designed for broadband amplifier applications in commercial and amateur communication equipment.

FEATURES:

- $P_G = 18$ dB min. at 75 W/30 MHz
- $IMD_3 = -30$ dBc max. at 75 W (PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.05 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA			35			V
BV_{CER}	$I_C = 50$ mA	$R_{BE} = 10$ Ω		60			V
BV_{EBO}	$I_E = 10$ mA			4.0			V
I_{CES}	$V_E = 28$ V					5	mA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 1.0$ A		10		100	---
C_{ob}	$V_{CB} = 28$ V	$f = 1.0$ MHz				80	pF
G_{PE}	$V_{CE} = 25$ V	$I_{CQ} = 3.2$ A	$f = 225$ MHz	13.5	14.5		dB
IMD_3	$P_{REF} = 16$ W	Vision = -8 dB Side Band = -16 dB	Snd. = -7 dB			-55	dBc